

Title (en)
COATING INFRA RED TRANSPARENT SEMICONDUCTOR MATERIAL

Publication
EP 0048542 B1 19851009 (EN)

Application
EP 81303328 A 19810721

Priority
GB 8027279 A 19800821

Abstract (en)
[origin: US4412903A] A shaped element of germanium or silicon is coated with a layer of hard infra red transparent carbon. The carbon is deposited on the element, used as a cathode, in a glow discharge charge chamber by applying a D.C. voltage to a hydrocarbon gas at a pressure of e.g. 10⁻¹ to 10⁻² Torr. Prior to depositing the carbon the element may be heated and cleaned using argon ion bombardment. Layers of germanium and silicon may also be deposited using the gases germane and silane respectively.

IPC 1-7
C23C 14/12; **C23C 14/38**; **G02B 1/10**

IPC 8 full level
C01B 31/06 (2006.01); **C23C 16/26** (2006.01); **C23C 16/27** (2006.01); **C23C 16/503** (2006.01); **C30B 29/04** (2006.01); **G02B 1/10** (2006.01); **H01L 21/302** (2006.01); **H01L 21/31** (2006.01); **H01L 31/0216** (2014.01)

CPC (source: EP US)
C23C 16/26 (2013.01 - EP US); **C23C 16/503** (2013.01 - EP US); **G02B 1/105** (2020.05 - EP); **G02B 1/111** (2013.01 - EP US); **G02B 1/14** (2015.01 - EP US); **H01L 31/02161** (2013.01 - EP US); **Y10T 428/30** (2015.01 - EP US)

Cited by
FR2514743A1; GB2291888A; GB2291888B; GB2129833A

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US 4412903 A 19831101; DE 3172609 D1 19851114; EP 0048542 A2 19820331; EP 0048542 A3 19820428; EP 0048542 B1 19851009; EP 0048542 B2 19930331; JP H0319164 B2 19910314; JP S57111220 A 19820710

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